

IMEP-LAHC, UMR 5130

Equipe CMNE "Composants Micro-Nanoélectroniques"

Publications dans des conférences internationales (2008)

Année	Auteurs	Titre		Sigle	Conférence	Lieu, date	Actes
2008	E. Rauwel, F. Ducroquet, P. Rauwel, M.-G. Willinger, I. Matko, N. Pinna	Carboxylic acids as oxygen supplying agents for ALD of high k thin films		ALD	8th International Conference on Atomic Layer Deposition	Bruges, Belgique (29 juin - 2 juillet 2008)	Sans
2008	P. Febvre, D. Bouis, N. De Leo, M. Fretto, S. Maggi, A. Sosso and V. Lacquaniti	Assessment of Overdamped SNS Niobium-Based Josephson Junctions for Digital Applications		ASC	Applied Superconductivity Conference (ASC)	Chicago, USA (17-22 Aug. 2008)	Abstract booklet. Extended papers submitted to IEEE Transactions on Applied Superconductivity.
2008	E. Baggetta, S. Bouat, V. Michal, J.-C. Villégier, D. Renaud, C. Bornier, P. Febvre, R. Guelaz, P. Loumeau	Elaboration of NbN ADC Circuits on Large Area Wafers for HyperSCAN		ASC	Applied Superconductivity Conference (ASC)	Chicago, USA (17-22 Aug. 2008)	Abstract booklet. Extended papers submitted to IEEE Transactions on Applied Superconductivity.
2008	P. Febvre, V. Michal, R. Setzu, J.-C. Villégier	Evaluation of self-shunted NbN/TaN/NbN Josephson junctions for digital electronics		ASC	Applied Superconductivity Conference (ASC)	Chicago, USA (17-22 Aug. 2008)	Abstract booklet. Extended papers submitted to IEEE Transactions on Applied Superconductivity.
2008	R. Guelaz, P. Desgreys, P. Loumeau and P. Febvre	RSFQ comparator behaviour modelling for sigma-delta bandpass ADC application with VHDL-AMS		DCIS	Conference on Design of Circuits and Integrated Systems	Grenoble (12-14 Nov. 2008)	
2008	K. Rogdakis, S.Y. Lee, D.J. Ki, S.K. Lee, E. Bano, K. Zekentes	Effect of Source and Drain contacts Schottky Barrier on 3C-SiC nanowire FETs I-V characteristics		ECSCRM	European Conference of Silicon Carbide and Related Materials (ECSCRM'08)	Barcelona, Spain (7-11 Sept. 2008)	Abstract booklet. Extended papers submitted to Materials Science Forum.
2008	F. Balestra, E. Parker, D. Leadley, S. Mantl, E. Dubois, O. Engstrom, R. Clerc, S. Cristoloveanu, H. Kurz, J.P. Raskin, M. Lemme, A. Ionescu, E. Kasper, A. Karmous, M. Baus, B. Spangenberg, M. Ostling, E. Sangiogi, G. Ghibaudo, D. Flandre	NANOSIL Network of Excellence: Silicon-based nanostructures and nanodevices for long-term nanoelectronics applications.	Invited paper	E-MRS	European Materials Research Society (E-MRS 2008), Symposium J	Strasbourg, France (26-30 May 2008)	Abstract booklet. Extended papers in Materials Science in Semiconductor Processing after review.

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2008	B. Vincent, J.F. Damlencourt, Y. Morand, A. Pouydebasque, C. Le Royer, L. Clavelier, N. Dechoux, P. Rivallini, T. Nguyen, S. Cristoloveanu, Y. Campidelli, D. Rouchon, M. Mermoux, S. Deleonibus, D. Bensahel, T. Billon	The Ge condensation technique: a solution for planar SOI/GeOI co-integration for advanced CMOS technologies?	Invited paper, European Materials Research Society Young Scientist Award	E-MRS	European Materials Research Society (E-MRS 2008), Symposium J	Strasbourg, France (26-30 mai 2008)	Abstract booklet. Extended papers in Materials Science in Semiconductor Processing after review.
2008	D. Bouis and P. Febvre	Microwave antennas for short distance communications in cryogenic systems		ESA	30th ESA Antenna Workshop on Antennas for Earth Observation, Science, Telecommunication and Navigation Space Missions	Noordwijk, The Netherlands (27-30 May 2008)	Proc. pp. 134-137
2008	M. Diop, N. Revil, M. Marin, F. Monsieur, P. Chevalier and G. Ghibaudo	Impact of Inside Spacer Process on Fully Self-Aligned 250 GHz SiGe:C HBTs Reliability Performances: a - Si vs. Nitride.		ESREF	European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF)	Maastricht, The Netherlands (Sept. 2008)	Abstract booklet
2008	G. Beylier, S. Bruyère, D. Benoit, G. Ghibaudo	Impact of Silicon nitride CESL on NLDEMOS transistor reliability.		ESREF	European Symposium on Reliability of Electron Devices, Failure Physics and Analysis (ESREF)	Maastricht, The Netherlands (Sept. 2008)	Abstract booklet
2008	C. Dupre, T. Ernst, E. Bernard, B. Guillaumot, N. Vulliet, P. Coronel, T. Skotnicki, S. Cristoloveanu, G. Ghibaudo, S. Deleonibus	A mobility extraction method for 3D multichannel devices.	Young scientist award	ESSDERC	38th European Solid-State Device Research Conference (ESSDERC'08)	Edinburgh, UK (15-19 Sept 2008)	Proc. of ESSDERC 2008, S. Hall, A. Walton eds., Institute of Physics, ISBN 978-1-4244-2363-7, pp. 230-233 (Sept. 2008)
2008	W. Van Den Daele, E. Augendre, L. Clavelier, E. Guiot, F. Allibert, S. Cristoloveanu	Advanced GeOI structures: from material properties to high performance pMOSFETs.		ESSDERC	ESSDERC Fringe, 38th European Solid-State Device Research Conference (ESSDERC'08),	Edinburgh, UK (15-19 Sept 2008)	Sans
2008	S. Cristoloveanu	Characterization methods for nanodevices.	Invited paper	ESSDERC	ESSDERC Workshop 'Si-Based Nanodevices for Ultimate CMOS and Beyond-CMOS', 38th European Solid-State Device Research Conference (ESSDERC'08)	Edinburgh, UK (15-19 Sept 2008)	Sans

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2008	G. Bidal, N. Loudet, C. Fenouillet-Beranger, S. Denorme, P. Perreau, D. Chanemougame, C. Laviron, F. Leverd, S. Barnola, R. Beneyton, C. Duluard, J.D. Chapon, P. Gouraud, T. Salvétat, M. Grosjean, E. Deloffre, D. Fleury, L. Clement, C. Pribat, R. Pantel, S. Monfray, D. Dutartre, G. Ghibardo, F. Boeuf, and T. Skotnicki	Folded Fully Depleted Bulk+ Technology as a Highly W-Scaled Planar Solution.		ESSDERC	38th European Solid-State Device Research Conference (ESSDERC'08)	Edinburgh, UK (15-19 Sept 2008)	Proc. of ESSDERC 2008, S. Hall, A. Walton eds., Institute of Physics, ISBN 978-1-4244-2363-7, pp. 210-213 (Sept. 2008)
2008	C. Buran, M.G. Pala, M. Mouis, M. Bescond, M. Michelini, L. Raymond	Full 3D real-space NEGF simulation of transport and magnetotransport in Si-Nanowire FETs	Poster	ESSDERC	ESSDERC Fringe, 38th European Solid-State Device Research Conference (ESSDERC'08).	Edinburgh, UK (15-19 Sept 2008)	Sans
2008	L. Gerrer, G. Ghibardo, J. Jomaah, G. Ribes	Impact of Oxide Progressive Soft Breakdown: Experiment and Modeling.		ESSDERC	ESSDERC Fringe, 38th European Solid-State Device Research Conference (ESSDERC'08).	Edinburgh, UK (15-19 Sept 2008)	Sans
2008	M. Bocquet, G. Molas, L. Perniola, X. Garros, J. Buckley, M. Gély, J.-P. Colonna, H. Grampeix, F. Martin, V. Vidal, A. Toffoli, B. De Salvo, S. Deleonibus, G. Pananakakis, G. Ghibardo	On the Role of a HTO/Al ₂ O ₃ Bi-Layer Blocking Oxide in Nitride-Trap Non-Volatile Memories.		ESSDERC	38th European Solid-State Device Research Conference (ESSDERC'08)	Edinburgh, UK (15-19 Sept 2008)	Proc. of ESSDERC 2008, S. Hall, A. Walton eds., Institute of Physics, ISBN 978-1-4244-2363-7, pp. 119-122 (Sept. 2008)
2008	T. Pro, J. Buckley, R. Barattin, A. Calborean, M. Gély, K. Huang, G. Delapierre, F. Duclairoir, E. Jalaguier, P. Maldivi, B. De Salvo, S. Deleonibus, G. Ghibardo.	Study of Ferrocene/Silicon Hybrid Memories: Influence of the Chemical Linkers and Device Thermal Stability.		ESSDERC	38th European Solid-State Device Research Conference (ESSDERC'08)	Edinburgh, UK (15-19 Sept 2008)	Proc. of ESSDERC 2008, S. Hall, A. Walton eds., Institute of Physics, ISBN 978-1-4244-2363-7, pp. 226-229 (Sept. 2008)
2008	P. Febvre et al	Digital SQUIDs for applications in Geophysics		EuroFlux	1st EUROFLUX Symposium	Naples, Italy (29 Sept.-1 Oct. 2008)	

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2008	J. Kunert, T. Ortlepp, P. Febvre, L. Fritzsche, R. Solz, E. Il'ichev and H.-G. Meyer	FLUXONICS foundry fabrication of superconductor electronics		EuroFlux	1st EUROFLUX Symposium	Naples, Italy (29 Sept.-1 Oct. 2008)	
2008	Q. Raffay, R. Clerc, G. Pananakakis and G. Ghibaudo	Estimations of the Ion-Ioff Performances of Nano nMOSFETs with Alternative Channels Materials		Euro-SOI	4th EUROSIOI Workshop	Cork, Ireland (23-25 Jan 2008)	Proceeding p. 43-44.
2008	N. Rodriguez, S. Cristoloveanu, T. Nguyen, F. Gamiz	Impact of the top surface density of states on the characteristics of ultrathin SOI pseudo-MOSFETs.		Euro-SOI	4th EUROSIOI Workshop	Cork, Ireland (23-25 janvier 2008)	Abstract booklet
2008	J-P. Mazellier, O. Faynot, F. Andrieu, S. Cristoloveanu, S. Deleonibus	Introduction of diamond into advanced FDSOI CMOS.		Euro-SOI	4th EUROSIOI Workshop	Cork, Ireland (23-25 janvier 2008)	Abstract booklet
2008	C. Sampedro, F. Gamiz, A. Godoy, S. Cristoloveanu, I.M. Tienda-Luna	Study of ballisticity in SOI nano-MOSFETs at very low drain bias.		Euro-SOI	4th EUROSIOI Workshop	Cork, Ireland (23-25 janvier 2008)	Abstract booklet
2008	S. Cristoloveanu, J-P. Colinge, O. Faynot, C. Claeys, S. Okhonin, D. Bretegnier	What are the critical issues for SOI ?	Invited paper, panel session	Euro-SOI	4th EUROSIOI Workshop	Cork, Ireland (23-25 janvier 2008)	Abstract booklet
2008	B. Bercu, L. Montès, P. Morfouli	Silicon chip built-in heat spreader: characterization and optimization using integrated sensors		Euro-TWMTM	3rd European Advanced Technology Workshop on Micropackaging and Thermal Management	La Rochelle, France (30-31 Jan. 2008)	Sans
2008	Konstantinos Rogdakis, Seoung-Yong Lee, Marc Bescond, Dong-Joo Kim, Sang-Kwon Lee, Edwige Bano and Konstantinos Zekentes	Electrical properties of 3C-SiC nanowires		HETECH	17th European Workshop on Heterostructure Technology HETECH'08	Venice, Italy (3-5 Nov. 2008)	Abstract booklet
2008	J-F. Damlencourt, B. Vincent, C. Le Royer, P. Rivallin, E. Martinez, M.C. Roure, Y. Campidelli, D. Rouchon, T. Nguyen, S. Cristoloveanu, Y. Morand, S. Descombes, I. Clavelier	Ge-On-Insulator substrates formed by Ge condensation technique: fabrication, modeling and characterization.	Invited paper	ICEM	International Conference of Electronic Materials (ICEM 2008), Symposium C: Silicon and Group IV Materials and Devices for Electronics and Opto-Electronics	Sydney, Australia (28 juillet - 1 août 2008)	Sans

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2008	E. Nowak, L. Perniola, G. Ghibaudo, C. Jahan, P. Scheiblin, G. Reimbold, B. De Salvo, F. Boulanger	On the Influence of Fin Corner Rounding in 3D Nanocrystal Flash Memories.		ICMTD	Joint Non-Volatile Semiconductor Memory Workshop (23rd IEEE NVSMW) and International Conference on Memory Technology and Design (3rd ICMTD)	Opio, France (May 2008)	Proceedings of ICMTD, ISBN 1-4244-1546-2, IEEE, pp. 61-63 (May 2008)
2008	J. Buckley, T. Pro, R. Barattin, A. Calborean, M. Gély, K. Huang, G. Delapierre, G. Ghibaudo, F. Duclairoir, E. Jalaguier, P. Maldivi, B. De Salvo and S. Deleonibus	On the Influence of Molecular Linker on Charge Transfer Rate in Hybrid Molecular (Ferrocene)/Silicon Field Effect Memories.		ICMTD	Joint Non-Volatile Semiconductor Memory Workshop (23rd IEEE NVSMW) and International Conference on Memory Technology and Design (3rd ICMTD)	Opio, France (May 2008)	Proceedings of ICMTD, ISBN 1-4244-1546-2, IEEE, pp. 68-71 (May 2008)
2008	D. Fleury, A. Cros, H. Brut and G. Ghibaudo	New Y-Function-Based Methodology for Accurate Extraction of Electrical Parameters on Nano-Scaled MOSFETs		ICMTS	IEEE Int. Conf. Microelectronics Test Structure, ICMTS	Edinburgh, Scotland (24-27 March 2008)	Proceedings of ICMTS, ISBN 978-1-4244-1800-8, IEEE, pp. 160-165 (2008)
2008	A. Cathignol, S. Mennillo, S. Bordez, L. Vendrame, G. Ghibaudo	Spacing Impact on MOSFET Mismatch		ICMTS	IEEE International Conference on Microelectronics Test Structures	Edinburgh, Scotland (24-27 March 2008)	Proceedings of ICMTS, ISBN 978-1-4244-1800-8, IEEE, pp. 90-95 (2008)
2008	B. Hackens, F. Martins, M. G. Pala, H. Sellier, T. Ouisse, X. Wallart, S. Bollaert, A. Cappy, V. Bavot, S. Huant	Imaging the electron local density of states inside buried semiconductor quantum rings		ICPS	29th Conference on the Physics of Semiconductors	Rio de Janeiro, Brasil (27 July-1 August 2008)	to be published in AIP Conference Proceedings Series
2008	M. Bescond, M. Lannoo, F. Michelini, N. Cavassilas, M. G. Pala	Quantum transport in nanowire metal-oxide-semiconductor transistors: influence of dielectric confinement		ICPS	29th Conference on the Physics of Semiconductors	Rio de Janeiro, July 27- August 1, 2008	to be published in AIP Conference Proceedings Series
2008	F. Balestra	Status and trends in Nanoscale Si-based devices and materials	Invited paper	ICSICT	9th International Conference on Solid-State and Integrated-Circuit Technology	Beijing, China (October 20-23, 2008)	Proceedings ICSICT, ISBN 978-1-4244-2185-5, IEEE, pp. 33-36 (2008)
2008	T. Reich, P. Febvre, Th. Ortlepp, F.H. Uhlmann, J. Kunert, R. Stolz, H.G. Meyer, R. Blancon, M. Auguste, D. Boyer, A. Cavaillou and G. Wavrand	First tests of digital SQUID magnetometers at LSBB		iDUST	2nd International Conference on Underground Science: iDUST – Interdisciplinary Deep Underground Science and Technology conference	Rustrel, France (2-4 Apr. 2008)	Sans

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2008	C. Dupré, A. Hubert, S. Bécu, M. Jublot, V. Maffini-Alvaro, C. Vizios, F. Aussenac, C. Arvet, S. Barnola, J.-M. Hartmann, G. Garnier, F. Allain, J.-P. Colonna, M. Rivoire, L. Baud, S. Pauliac, V. Loup, P. Rivallin, G. Ghibaudo, O. Faynot, T. Ernst and S. Deleonibus,	15nm-diameter 3D Stacked Nanowires with optional Independent Gates operation (?FET).		IEDM	IEEE International Electron Devices Meeting	San Francisco, USA (15-17 Dec. 2008).	Digest of Technical Papers, pp. 749-752 (Dec. 2008)
2008	E. Batail, S. Monfray, C. Tabone, O. Kermarrec, J.F. Damlencourt, P. Gautier, G. Rabile, C. Arvet, N. Loubet, Y. Campidelli, J.M. Hartman, A. Poydebasque, V. Delaye, C. Le Royer, G. Ghibaudo, T. Skotnicki, S. Deleonibus	Localized ultra-thin GeOI: An innovative approach to germanium channel MOSFETs on bul Si substrates		IEDM	IEEE International Electron Devices Meeting	San Francisco, USA (15-17 Dec. 2008)	Digest of Technical Papers, pp. 397-400 (Dec. 2008)
2008	E. Nowak, M. Bocquet, L. Perniola, G. Ghibaudo, G. Molas, C. Jahan, R. Kies, G. Reibold, B. De Salvo, F. Boulanger	New Physical Model for ultra-scaled 3D Nitride-Trapping Non-Volatile Memories.		IEDM	IEEE International Electron Devices Meeting	San Francisco, USA (15-17 Dec. 2008).	Digest of Technical Papers, pp. 559-562 (Dec. 2008)
2008	M. Rafik, G. Ribes, G. Ghibaudo,	Contributions and Limits of Charge Pumping Measurement for Addressing Trap Generation in High-K/SiO ₂ Dielectric Stacks.		IRPS	IEEE Int. Reliability Physics Symposium (IRPS)	Phoenix, Arizona, USA (April 2008)	Proceedings of IRPS, IEEE Catalog No. CFP08RPS-PRT, pp. 341-346 (2008)
2008	V. Martinez, C. Besset, F. Monsieur, D. Ney, L. Montès, G. Ghibaudo	New insight into tantalum pentoxide metal-insulator-metal (MIM) capacitors: Leakage current modeling, self-heating, reliability assessment and industrial applications		IRPS	46th Annual IEEE International Reliability Physics Symposium	27 April - 1 May 2008, Phoenix, USA	Proceedings of IRPS, IEEE Catalog No. CFP08RPS-PRT, pp. 225-229 (2008)
2008	D. Lopez, F. Monsieur, F. Balestra	Ageing under illumination of MOS transistors for active pixel sensors (APS) applications		IRW	IEEE International Integrated Reliability Workshop (IRW)	South Lake Tahoe, USA (12-16 Oct. 2008)	IRW Final report, ISBN 078-1-4244-2104-7, IEEE, pp. 36-39 (2008)

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2008	M. Diop, N. Revil, M. Marin, F. Monsieur, T. Schwartzmann and G. Ghibaudo	Coupled Approach for Reliability Study of Fully Self Aligned SiGe:C 250GHz HBTs.		IRW	IEEE International Integrated Reliability Workshop (IRW)	South Lake Tahoe, USA (12-16 Oct. 2008)	IRW Final report, ISBN 078-1-4244-2104-7, IEEE, pp. 77-80 (2008)
2008	V. Martinez, C. Besset, F. Monsieur, L. Montès, G. Ghibaudo	Impact of Oxygen Vacancies Profile and Fringe Effect on Leakage Current Instability of Tantalum Pentoxide Metal-Insulator-Metal (MIM) Capacitors		IRW	IEEE International Integrated Reliability Workshop (IRW)	South Lake Tahoe, USA (12-16 Oct. 2008)	IRW Final report, ISBN 078-1-4244-2104-7, IEEE, pp. 21-24 (2008)
2008	E. Buccafurri, R. Clerc, F. Calmon, M. Pala, A. Poncet and G. Ghibaudo	Performances Comparison of Si and GaAs Based Resonant Tunneling Diodes		ISCS	International Symposium on Compound Semiconductors	Europa-Park, Rust, Germany (September 21-24, 2008)	Sans
2008	V. Martinez, C. Besset, F. Monsieur, D. Ney, L. Montès, G. Ghibaudo	How to Monitor Metal-Insulator-Metal (MIM) Capacitors Dielectric Reliability.	Best student paper	MIEL	26th International Conference on Microelectronics, MIEL	Nis, Serbia (11-14 May 2008)	Proc. MIEL, ISBN 978-1-4244-1882-4, IEEE, pp. 537-540 (2008)
2008	D. Lopez, F. Monsieur, F. Balestra,	MOS capacitors characterization under illumination,		MIEL	26th International Conference on Microelectronics (MIEL 2008)	Nis, Serbia, 11-14 May 2008	Proc. MIEL, ISBN 978-1-4244-1882-4, IEEE, pp. 583-585 (2008)
2008	B. Bercu, X. Xu, L. Montès, P. Morfouli	Characterization of mechanical stress on nanostructures for NEMS applications by ultrathin-membrane and self-suspension techniques		MNE	34th International Conference on Micro and Nano Engineering (MNE 2008)	Athens, Greece (15-18 Sept. 2008)	Abstract booklet, 1 page. Extended papers submitted to Microelectronic Engineering.
2008	X. Xu , B. Bercu, L. Montès	On the interest of mechanical stress in a tunnel junction nanostructure for innovative NEMS pressure sensor		MNE	34th International Conference on Micro and Nano Engineering (MNE 2008)	Athens, Greece (15-18 Sept. 2008)	Abstract booklet, 1 page. Extended papers submitted to Microelectronic Engineering.
2008	A. Fardoun, M. K. Hassan, H.N. Mohammed, and J. Jomaah	SOI MOSFETs as Potential Replacement of Mechanical Relays in Electrical Systems		MWSCAS	2008 IEEE Midwest Symposium on Circuits and Systems (NWCAS)	Knoxville, USA (August 2008)	IEEE Conference Proceedings, MWSCAS 2008, pp. 718-721, DOI: 10.1109/MWSCAS.2008.4616900 (2008)
2008	P. Martin, M. Cavelier, R. Fascio and G. Ghibaudo	MOSFET Compact Modeling Issues for Low Temperature (77 K - 200 K) Operation.		Nanotech-WCM	NSTI Nanotech 2008, Workshop on Compact Modeling (WCM 2008)	Boston, Massachusetts, U.S.A. (June 2008)	Proceedings in Nanotech 2008, Vol. 3, ISBN 978-1-4200-8505-1, pp.865-868 (2008)
2008	S. Huant, F. Martins, M. G. Pala, B. Hackens, H. Sellier, T. Ouisse, V. Bayot	Scanning-Gate Microscopy images the electronic LDOS inside nanostructures		NC-AFM	11th International Conference on Non-contact Atomic Force Microscopy (NCAFM-2008)	Madrid, September 16-19, 2008	Extended paper submitted to Nanotechnology.

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2008	V. Gouttenoire, P. Vincent, A. Ayari, S. Perisanu, J.-M. Benoit, M. Choueib, N. Blanchard, S.T. Purcell, J. L. Leclerc, P. Cremilleu, R. Mazurczyk, G. Bremond, L. Montès	Exploitation of new phenomena in nanoelectromechanical systems and realization of a tunable nanoresonator	Best student paper award	NT	9th International Conference on the Science and Application of Nanotubes	Montpellier, France (29 June 29 - 4 July 2008)	Sans
2008	D. Raully, A. Monfardini, A. Colin and P. Febvre	Design of Two-band 150-220 GHz Superconducting Bolometric Detection Structure		PIERS Online	Progress in Electromagnetics Research Symposium (PIERS)	Cambridge, USA. (2-6 July 2008)	Vol. 4, No. 6, pp. 671-675
2008	E. Rauwel, F. Ducroquet, P. Rauwel, M.-G. Willinger, I. Matko, D. Kiselev, N. Pinna	Carboxylic Acids as Oxygen Supplying Agents for Atomic Layer Deposition of High-k Thin Films		PRiME	Pacific Rim Meeting on Electrochemical and Solid-State Science, Joint Meeting (214th Meeting of the Electrochemical Soc. and 2008 Fall Meeting of the Electrochemical Soc. of Japan), Symposium: E2 - Atomic Layer Deposition	Honolulu, Hawaii, USA (12-17 oct. 2008)	Proc. in ECS Transactions, Vol.16, no.4, pp. 279-289 (2008)
2008	K-I. Na, S. Cristoloveanu, Y-H. Bae, W. Xiong, C.R. Cleavelin, P. Patruno, J-H. Lee	Coupling and short-channel effect with gate-drain distance and gate lengths in triple-gate MOSFETs based on silicon-on-insulator (SOI) substrate.		PRiME	Joint Meeting (214th Meeting of the Electrochemical Soc. and 2008 Fall Meeting of the Electrochemical Soc. of Japan), Symposium E1 'Solid State Divisions General Session'	Honolulu, Hawaii, USA (12-17 oct. 2008)	
2008	L. Souriau, T. Nguyen, E. Augendre, R. Loo, V. Terzieva, M. Caymax, S. Cristoloveanu, M. Meuris, W. Vandervorst	High hole mobility SGOI substrates obtained by the germanium condensation technique.		PRiME	3rd Int. Symp. on SiGe, Ge and Related Compounds: Materials, Processing, and Devices, Joint Meeting (214th ECS Meeting and 2008 Fall Meeting of the Electrochemical Soc. of Japan)	Honolulu, Hawaii, USA (12-17 oct. 2008)	Proc. in ECS Transactions, Vol.16, no.10, 79-89 (2008)

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2008	M. Kostrzewa, T. Nguyen, J. Mazellier, C. Deguet, L. Clavelier, K. Landry, S. Cristoloveanu	Tuning the electrostatic properties of silicon-on-insulating multilayer (SOIM) structures.		PRiME	10th Int. Symp. on Semiconductor Wafer Bonding: Science, Technology, and Applications, Joint Meeting (214th ECS Meeting and 2008 Fall Meeting of the Electrochemical Soc. of Japan)	Honolulu, Hawaii, USA (12-17 oct. 2008)	
2008	G. Molas, M. Bocquet, H. Grampeix, J. P. Colonna, L. Masarotto, C. Licitra, N. Rochat, T. Veyron, F. Martin, M. Gély, C. Bongiorno, S. Lombardo, G. Pananakakis, G. Ghibaudo, B. De Salvo.	Reliability of charge trapping memories with high-k control dielectrics	Invited paper	Sematech	5th International Symposium on Advanced Gate Stack Technology	Austin, Texas (Sept 2008)	Sans
2008	E. Batail, S. Monfray, A. Pouydebasque, G. Ghibaudo, and T. Skotnicki	Impact of scaling on electrostatics of germanium-channel MOSFET-analytical study.		Silicon Nanoelectronics Workshop	IEEE Silicon Nanoelectronics Workshop	Honolulu (June 15-16, 2008)	Sans. Conference workbook.
2008	M. Ferrier, D. Zhang, P. Griffin, R. Clerc, S. Monfray, T. Skotnicki, and Y. Nishi,	Theoretical investigation and analytical modeling of metal insulator metal gate controlled tunneling behavior		Silicon Nanoelectronics Workshop	IEEE Silicon Nanoelectronics Workshop	Honolulu (June 15-16, 2008)	Sans. Conference workbook.
2008	M.A. Negara, K. Cherkaoui, C.D. Young, P. Majhi, W. Tsai, D. Bauza, G. Ghibaudo and P.K. Hurley	Analysis of Electron Mobility in HfO ₂ /TiN MOSFETs: The influence of HfO ₂ thickness, Temperature and Oxide Charge		SISC	IEEE Semiconductor Interface Specialists Conference	San Diego, USA, December 11-13, 2008	Sans - mais très sélectif
2008	N. Rodriguez, S. Cristoloveanu, F. Gamiz	A revisited pseudo-MOSFET model for ultrathin SOI films.		SOI Conf	2008 IEEE International SOI Conference	New Paltz, New York, USA (6-9 oct. 2008)	2008 IEEE International SOI conference proceedings, ISBN 978-1-4244-1954-8, pp. 65-66 (2008)
2008	L. Pham-Nguyen, C. Fenouillet-Beranger, A. Vandooren, A. Wild, G. Ghibaudo, S. Cristoloveanu	Direct comparison of Si/High-K and Si/SiO ₂ channels in advanced FD SOI MOSFETs.		SOI Conf	2008 IEEE International SOI Conference	New Paltz, New York, USA (6-9 Oct. 2008)	2008 IEEE International SOI conference proceedings, ISBN 978-1-4244-1954-8, pp. 25-26 (2008)
2008	G. Hamaide, F. Allibert, S. Cristoloveanu	Impact of surface and buried interface passivation on ultrathin SOI electrical properties.		SOI Conf	2008 IEEE International SOI Conference	New Paltz, New York, USA (6-9 oct. 2008)	2008 IEEE International SOI conference proceedings, ISBN 978-1-4244-1954-8, pp. 145-146 (2008)

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2008	Q-T. Nguyen, J.F. Damlencourt, B. Vincent, V. Loup, Y. Le Cunff, P. Gentil, S. Cristoloveanu	SOI-GeOI hybrid substrates elaboration by Ge condensation ;: process and electrical properties.		SOI Conf	2008 IEEE International SOI Conference	New Paltz, New York, USA (6-9 oct. 2008)	2008 IEEE International SOI conference proceedings, ISBN 978-1-4244-1954-8, pp. 103-104 (2008)
2008	G. Bidal, F. Boeuf, F. Payet, S. Denorme, N. Loubet, P. Perreau, C. Mezzomo, M. Marin, D. Fleury, C. Leyris, F. Leverd, P. Gouraud, C. Laviron, R. Beneyton, A. Torres, B. Imbert, D. Delille, L. Clement, G. Ghibaudo, T. Skotnicki	Pushing Bulk Transistor with Conventional SiON Gate Oxide for Low Power Applications.		SSDM	International Conference on Solid State Devices and Materials (SSDM)	Tsukuba, Japan (23-26 Sept. 2008)	Conference book.
2008	Q. Raffhay, R. Clerc, G. Pananakakis and G. Ghibaudo	Source-to-Drain vs. Band-to-Band Tunneling in Ultra-Scaled DG nMOSFETs with Alternative Channel Materials		SSDM	International Conference on Solid State Devices and Materials (SSDM)	Tsukuba, Japan (23-26 Sept. 2008)	Conference book.
2008	B. Bercu, L. Montès, P. Morfouli	Silicon integrated vapor chamber equipped with integrated sensor network for in-situ thermal monitoring and cooling optimization		THERMINIC	14th International Workshop on Thermal Investigation of ICs and Systems	Roma, Italy (24-26 Sept. 2008)	Proc. of THERMINIC, ISBN 978-2-35500-008-9, pp. 173-176 (2008)
2008	R. Clerc, P. Palestri, L. Selmi, G. Ghibaudo,	Back-Scattering in Quasi-Ballistic NanoMOSFETs: The role of Non Thermal Carrier Distributions		ULIS	Int. Conference on Ultimate Integration of Silicon	Udine, Italy (13-14 March 2008)	Proceedings of ULIS 2008, IEEE, pp. 125-128
2008	V. Quenette, P. Lemoigne, D. Rideau, R. Clerc, L. Ciampolini, M. Minondo, C. Tavernier, H. Jaouen.	Electrical Characterization and Compact Modeling of MOSFET body effect		ULIS	Int. Conference on Ultimate Integration of Silicon	Udine, Italy (13-14 March 2008)	Proceedings of ULIS 2008, IEEE, pp. 163-166
2008	C. Dupré, T. Ernst, S. Borel, Y. Morand, S. Descombes, B. Guillaumot, X. Garros, S. Becu, X. Mescot, G. Ghibaudo, S. Deleonibus	Impact of isotropic plasma etching on channel Si surface roughness measured by AFM and on NMOS inversion layer mobility		ULIS	Int. Conference on Ultimate Integration of Silicon	Udine, Italy (12-14 March 2008)	Proceedings of ULIS 2008, IEEE, pp. 133-136

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2008	M. Collonge, M. Vinet, S. Deleonibus, G. Ghibaudo	Nano Accumulation-Mode Suspended-Gate MOSFET: Impact of adhesion forces on electro-mechanical characteristics.		ULIS	Int. Conference on Ultimate Integration of Silicon	Udine, Italy (12-14 March 2008)	Proceedings of ULIS 2008, IEEE, pp. 125-128
2008	M. Cassé, F. Rochette, N. Bhourri, F. Andrieu, D.K. Maude, M. Mouis, G. Reibold, F. Boulanger	Mobility of strained and unstrained short channel FD-SOI MOSFETs : New insight by magnetoresistance		VLSI Symposium	IEEE Symposium on VLSI Technology (VLSI Symposium)	Hawaii, USA (17-19 June 2008).	IEEE VLSI Digest of Technical Papers, IEEE, pp.170-171 (available through ieeexplore)
2008	G. Bidal, F. Boeur, S. Denorme, N. Loubet, C. Laviron, F. Leverd, S. Barnola, T. Salvetat, V. Cosnier, F. Martin, M. Grosjean, P. Perreau, D. Chanemougame, S. Haendler, M. Marin, M. Rafik, D. Fleury, C. Leyris, L. Clement, M. Sellier, S. Monfray, J. Bougueon, M.P. Samson, J.D. Chapon, P. Gouraud, G.Ghibaudo and T. Skotnicki	Planar Bulk+ Technology using TiN/Hf-based gate stack for Low Power Applications.		VLSI Symposium	IEEE Symposium on VLSI Technology (VLSI Symposium)	Hawaii, USA (17-19 June 2008).	IEEE VLSI Digest of Technical Papers, IEEE, pp.146-147 (available through ieeexplore)
2008	E. Rauwel, F. Ducroquet, G. Clavel, P. Rauwel, M.-G. Willinger, I. Matko, N. Pinna	ALD of High-k thin films using carboxylic acids as oxygen supplying agents		WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (june 2008).	Sans. Conference workbook, session 9, p. 93. Selected for publication in JVST.
2008	J. Coignus, R. Clerc, C. Leroux, G. Reibold and G. Ghibaudo	Analytical Modeling of Tunneling Current Through SiO ₂ -HfO ₂ Stacks in MOS Structures		WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (23 - 25 June 2008)	Sans. Selected for publication in JVST.
2008	G. Beylier, D. Benoit, P. Mora, S. Bruyère, G. Ghibaudo,	Contact etch stop a-Si ₃ N ₄ :H layer: a key factor for single polysilicon flash memory data retention.		WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (June 2008).	Sans. Selected for publication in JVST.
2008	N. Guénifi, O. Ghobar, D. Bauza	Further evidences that PbO centers dominates Si-SiO ₂ interface traps in fully processed MOSFET's		WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (june 2008).	Sans. Conference workbook pp. 271-272.

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2008	C. Dubourdieu, V. Brizé, J. Ubrig, S. Margueron, I. Matko, E. Rauwel, F. Ducroquet, N. Rochat, A. Klein, B. Höllander	HfO ₂ -based solid solutions for high-k/metal gate stack properties improvement	Invited paper	WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (june 2008).	Sans. Conference workbook, session 9, p. 91.
2008	L. Gerrer, G. Ribes, G. Ghibaudo, J. Jomaah	Impact of Progressive Soft Oxide Breakdown on MOS Parameters: Experiment and Modelling.		WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (June 2008).	Sans. Selected for publication in JVST.
2008	L. Zafari, J. Jomaah, G. Ghibaudo, O. Faynot	Low Frequency Noise Analysis in HfO ₂ /SiO ₂ gate oxide Fully-Depelted SOI Transistors.		WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (june 2008).	Sans. Selected for publication in JVST.
2008	M. Rafik, G. Ribes, G. Ghibaudo	SiO ₂ Interfacial Layer as The Origin of The Breakdown of High-k Dielectric Stacks.		WODIM	15th Workshop on Dielectrics in Microelectronics	Berlin, Germany (june 2008).	Sans. Conference workbook.
2008	P. Martin, M. Cavelier, R. Fascio and G. Ghibaudo	EKV3 Compact Modeling of MOS transistors from a 0.18 μ m CMOS Technology for Mixed Analog-Digital Circuit Design at Low Temperature.		WOLTE	Eighth International Workshop on Low Temperature Electronics, WOLTE 8	Jena/Gabelbach, Germany (22-25 June 2008)	Sans.
2008	S. Feruglio, F. Andrieu, O. Faynot, P. Garda, and G. Ghibaudo	Low-Temperature Electrical Characterization of eXtra-strained FD-SOI n-MOSFETs with TiN/HfO ₂ gate stack for the 32nm Technology Node.		WOLTE	Eighth International Workshop on Low Temperature Electronics, WOLTE 8	Jena/Gabelbach, Germany (22-25 June 2008)	Sans.
2008	P. Febvre, T. Reich, H. Toepfer, J. Kunert, H.-G. Meyer, T. Ortlepp and F.-H. Uhlmann	RSFQ circuit with integrated synchronisation cell		WOLTE	Eighth International Workshop on Low Temperature Electronics, WOLTE 8	Jena/Gabelbach, Germany (22-25 June 2008)	Sans.